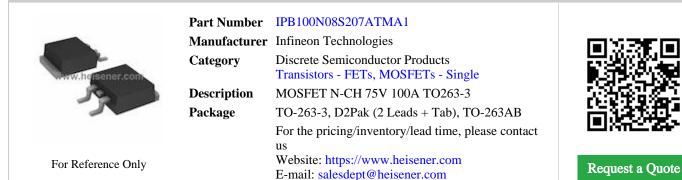


IPB100N08S207ATMA1

IPB100N08S207ATMA1 Information



Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



IPB100N08S207ATMA1 Specifications

Manufacturer Part Number	IPB100N08S207ATMA1	
Manufacturer	Infineon Technologies	
Category	Discrete Semiconductor Products	
	Transistors - FETs, MOSFETs - Single	
Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
Series	OptiMOS?	
FET Type	N-Channel	
Technology	MOSFET (Metal Oxide)	
Drain to Source Voltage (Vdss)	75V	
Current - Continuous Drain (Id) @ 25°C	100A (Tc)	
Drive Voltage (Max Rds On, Min Rds On)	10 V	
Vgs(th) (Max) @ Id	4V @ 250µA	
Gate Charge (Qg) (Max) @ Vgs	200nC @ 10V	
Input Capacitance (Ciss) (Max) @ Vds	4700pF @ 25V	
Vgs (Max)	±20V	
FET Feature	-	
Power Dissipation (Max)	300W (Tc)	
Rds On (Max) @ Id, Vgs	6.8 mOhm @ 80A, 10V	
Operating Temperature	-55°C ~ 175°C (TJ)	
Mounting Type	Surface Mount	
Supplier Device Package	PG-TO263-3-2	
Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	
		Report errors?

IPB100N08S207ATMA1 Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE BUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

IPB100N08S207ATMA1 Payment Methods



If you have any question about IPB100N08S207ATMA1, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com